## IN THE CLAIMS

- 1. (Currently Amended) A high frequency dielectric ceramics composition constituted by combining a combination of  $(Zn_{1-x}M_x)TiO_3$  and  $yTiO_2$  as a main component, into which one of 0~5 wt %  $B_2O_3$ , 0~5 wt %  $H_3BO_3$ , 0~5 wt %  $SiO_2$ - $K_2O$  glass, 0~5 wt %  $B_2O_3$  and  $SiO_2$ - $K_2O$  glass, or 0~5 wt %  $H_3BO_3$  and  $SiO_2$ - $K_2O$  glass is added as an additive, satisfies conditions of M is Mg, Co or Ni, 'x' is  $[0 \le x \le 0.55]$  or case of Mg and 'x' is  $[0 \le x \le 1.0]$  or  $[0 \le x \le 1.0]$  in case of Co, and  $[0 \le x \le 1.0]$  in case of Ni, and  $[0 \le y \le 0.6]$ .
- 2. (Original) A high frequency dielectric ceramics composition preparation method in which material powder of ZnO, MO (in this respect, MO is MgO, CoO or NiO) and TiO<sub>2</sub> is weighed according to a composition range of  $(Zn_{1-x}M_x)TiO_3$  and  $yTiO_2$  (M is one of Mg, Co and Ni, x is  $0 \le x \le 0.55$  in case of Mg, x is  $0 \le x \le 1$  in case of Co, x is  $0 \le x \le 1$  in case of Ni, and y is  $0 \le y \le 0.6$ ), mixed and dried,

the dried powder is calcined at a temperature of 850~950°C,

the calcined powder is mixed with one of  $0\sim5$  wt %  $B_2O_3$ ,  $0\sim5$  wt %  $H_3BO_3$ ,  $0\sim5$  wt %  $SiO_2$ - $K_2O$  glass,  $0\sim5$  wt %  $B_2O_3$  and  $SiO_2$ - $K_2O$  glass, or  $0\sim5$  wt %  $H_3BO_3$  and  $SiO_2$ - $K_2O$  glass as an additive,

the mixed powder is crushed,

the crushed power is shaped,

the shaped body is fired at a temperature of 800~925°C, and

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Serial No. 10/019,666 Docket No.300602002400  $(Zn_{1-x}M_x)TiO_3$  is calcined at a temperature corresponding to a region (region II) of below a phase dissociation temperature as shown in Figure 1 to obtain  $(Zn_{1-x}M_x)TiO_3$  (M is Mg, Co or Ni) of a single phase of rhombohedral/hexagonal crystal.

- 3. (Original) The method of claim 2, wherein the shaped body is made in a manner that an aqueous solution adding a PVA binder is sprayed onto the crushed powder to make a granule, to which a pressure is applied.
- 4. (Original) The method of claim 3, further comprises a step for maintaining the shaped body at a temperature of 300~500°C for a predetermined time and removing the binder.
- 5. (Original) The method of claim 2, wherein  $(Zn_{1-x}M_x)TiO_3$  is first calcined, and the calcined  $(Zn_{1-x}M_x)TiO_3$  is mixed with one of 0~5 wt %  $B_2O_3$ , 0~5 wt %  $H_3BO_3$ , 0~5 wt %  $SiO_2$ - $K_2O$  glass, 0~5 wt %  $B_2O_3$  and  $SiO_2$ - $K_2O$  glass, or 0~5 wt %  $H_3BO_3$  and  $SiO_2$ - $K_2O$  glass as an additive, and then fired.
- 6. (Currently Amended) A high frequency dielectric ceramics composition constituted by combining a combination ( $Zn_{1-a}Mg_{1-b}Co_{1-c}Ni_{1-d}$ )TiO<sub>3</sub> and yTiO<sub>2</sub> as a main component, into which one of 0~5 wt % B<sub>2</sub>O<sub>3</sub>, 0~5 wt % H<sub>3</sub>BO<sub>3</sub>, 0~5 wt % SiO<sub>2</sub>-K<sub>2</sub>O glass, 0~5 wt % B<sub>2</sub>O<sub>3</sub> and SiO<sub>2</sub>-K<sub>2</sub>O glass, or 0~5 wt % H<sub>3</sub>BO<sub>3</sub> and SiO<sub>2</sub>-K<sub>2</sub>O glass is added as an additive,

Serial No. 10/019,666 Docket No.300602002400 satisfies conditions of  $[0 \le a \le 1, 0 \le b \le 1, 0 \le c \le 1, 0 \le d \le 1]$  and  $0 \le y \le 0.6$   $0 < a \le 1, 0 < b \le 1, 0 < c \le 1$ ,  $0 < d \le 1$  and  $0 < y \le 0.6$ .

- 7. (Currently Amended) Various high frequency devices such as a stacked chip capacitor, a stacked chip filter, a stacked chip capacitor/inductor composite device and a module, a low temperature sintered board, a resonator and a filter or a ceramic antenna, are fabricated by using the dielectric High frequency devices comprising the composition of claim 1.
- 8. (New) The high frequency devices of claim 7, wherein the high frequency devices are selected from the group consisting of a stacked chip capacitor, a stacked chip filter, a stacked chip capacitor/inductor composite device and a module, a low-temperature sintered board, a resonator, a filter, a ceramic antenna and combinations thereof.

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